

Features

- Center amplifying gate
- Metal case with ceramic insulator
- Low on-state and switching losses

Typical Applications

- AC controllers
- DC and AC motor control
- Controlled rectifiers

I_{T(AV)} **3777 A**
V_{DRM/V_{RRM}} **4300-5200V**
I_{TSM} **45 kA**
I²t **10125 10³A²S**



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
I _{T(AV)}	Mean on-state current	180° half sine wave 50Hz Double side cooled,	125			3777	A
V _{DRM} V _{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	tp=10ms	125	4300		5200	V
I _{DRM} I _{RRM}	Repetitive peak current	at V _{DRM} at V _{RRM}	125			250	mA
I _{TSM}	Surge on-state current	10ms half sine wave	125			45	kA
I ² t	I ² t for fusing coordination	V _R =0.6V _{RRM}				10125	A ² s*10 ³
V _{TO}	Threshold voltage		125			0.96	V
r _T	On-state slope resistance					0.21	mΩ
V _{TM}	Peak on-state voltage	I _{TM} =3000A, F=90kN	125			1.59	V
dv/dt	Critical rate of rise of off-state voltage	V _{DM} =0.67V _{DRM}	125			1000	V/μs
di/dt	Critical rate of rise of on-state current	V _{DM} = 67%V _{DRM} to 4000A, Gate pulse t _r ≤0.5μs I _{GM} =1.5A	125			250	A/μs
Q _{rr}	Recovery charge	I _{TM} =2000A, tp=2000μs, di/dt=-20A/μs, V _R =50V	125		4000		μC
I _{GT}	Gate trigger current	V _A =12V, I _A =1A	25	40		300	mA
V _{GT}	Gate trigger voltage			0.8		3.0	V
I _H	Holding current			20		1000	mA
V _{GD}	Non-trigger gate voltage	V _{DM} =67%V _{DRM}	125	0.3			V
R _{th(j-c)}	Thermal resistance Junction to case	DC: double side cooled Clamping force 90kN				0.0050	°C /W
R _{th(c-h)}	Thermal resistance case to heatsink					0.0015	
F _m	Mounting force			81		108	kN
T _{stg}	Stored temperature			-40		140	°C
W _t	Weight				2000		g
Outline		P21					

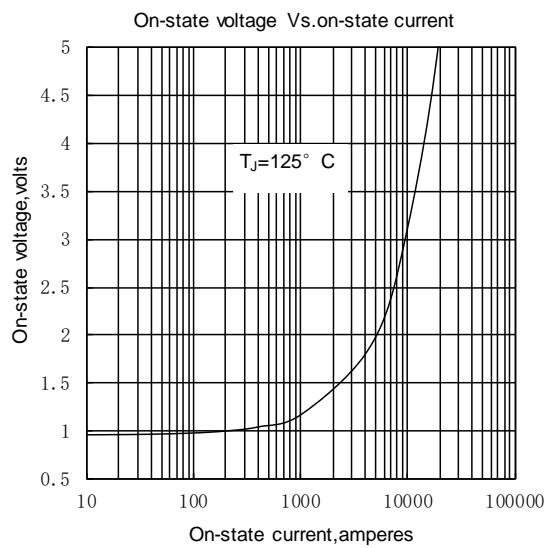


Fig.1

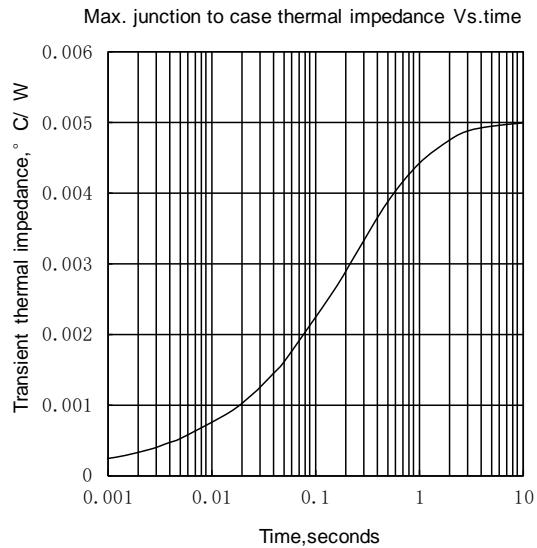


Fig.2

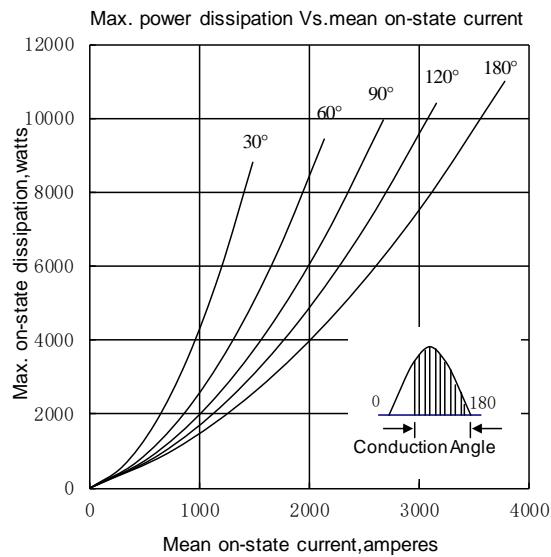


Fig.3

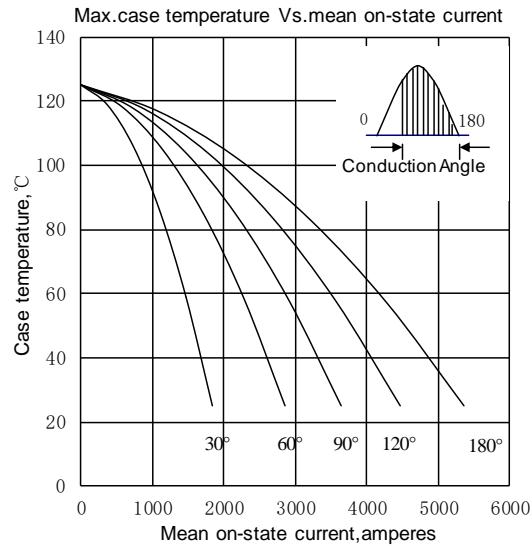


Fig.4

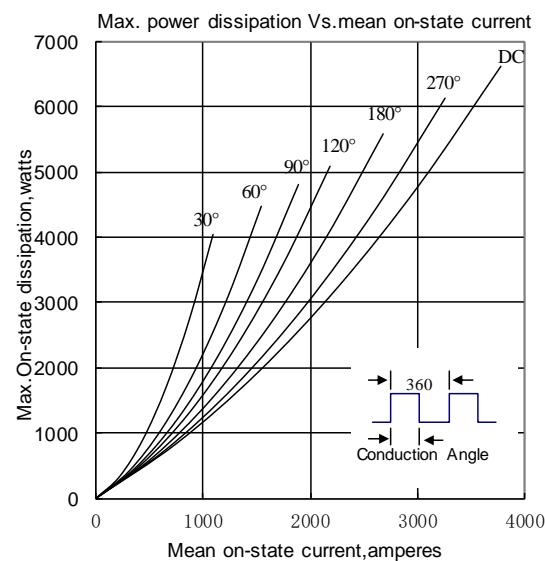


Fig.5

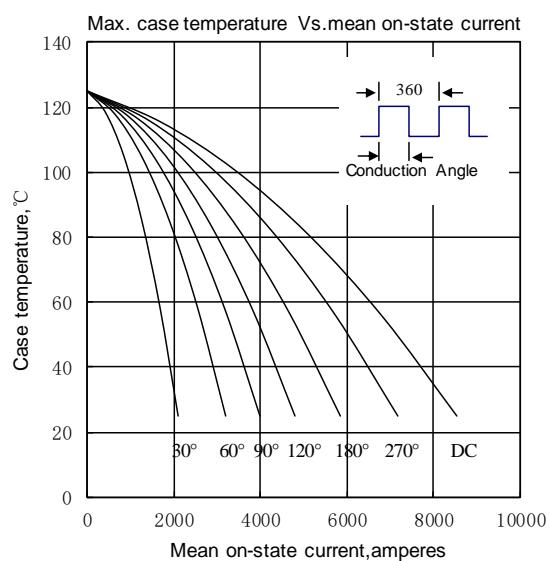


Fig.6

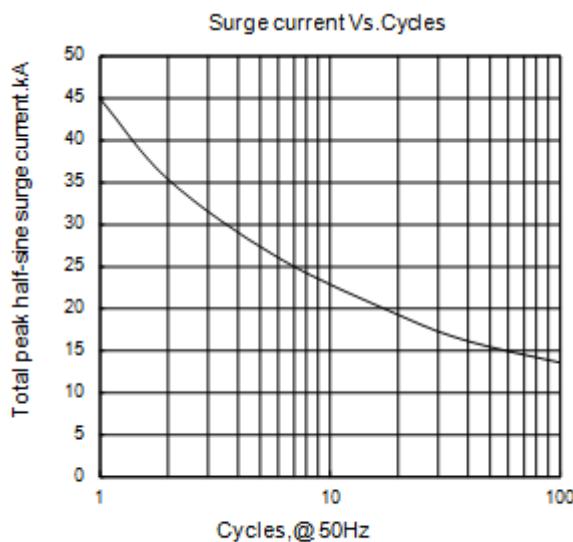


Fig 7

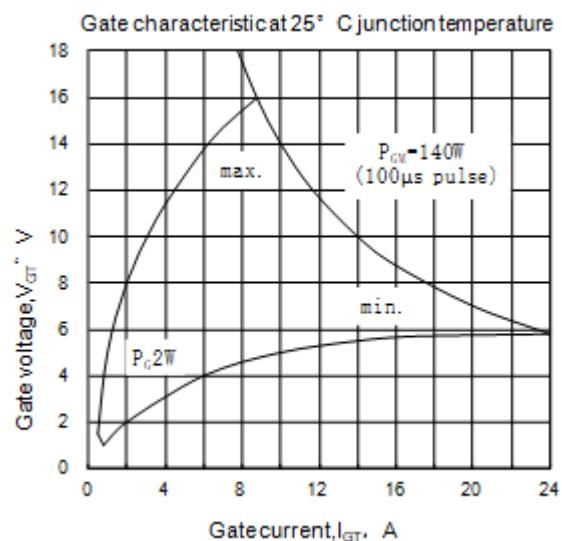


Fig 8

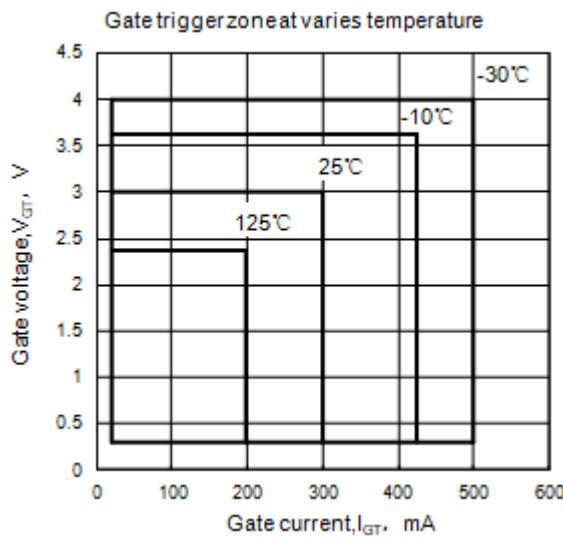


Fig 9

